Mohammad Wahidur Rahman

List of Publications by Year
in descending order

9	110	1478505 6	1588992 8
papers	citations	h-index	g-index

9	9	9	163
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Linearity Improvement With AlGaN Polarization- Graded Field Effect Transistors With Low Pressure Chemical Vapor Deposition Grown SiN_x Passivation. IEEE Electron Device Letters, 2020, 41, 19-22.	3.9	36
2	Design and Fabrication of Vertical GaN p-n Diode With Step-Etched Triple-Zone Junction Termination Extension. IEEE Transactions on Electron Devices, 2020, 67, 3553-3557.	3.0	17
3	BaTiO3/Al0.58Ga0.42N lateral heterojunction diodes with breakdown field exceeding 8 MV/cm. Applied Physics Letters, 2020, 116, .	3.3	17
4	Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High-k Bismuth Zinc Niobate Oxide. IEEE Transactions on Electron Devices, 2021, 68, 3333-3338.	3.0	14
5	Integration of high permittivity BaTiO3 with AlGaN/GaN for near-theoretical breakdown field kV-class transistors. Applied Physics Letters, 2021, 119, .	3.3	11
6	High-permittivity dielectric edge termination for vertical high voltage devices. Journal of Computational Electronics, 2020, 19, 1538-1545.	2.5	7
7	Hybrid BaTiO3/SiNx/AlGaN/GaN lateral Schottky barrier diodes with low turn-on and high breakdown performance. Applied Physics Letters, 2021, 119, 013504.	3.3	6
8	Local electric field measurement in GaN diodes by exciton Franzâ€“Keldysh photocurrent spectroscopy. Applied Physics Letters, 2020, 116, .	3.3	2
9	Demonstration of BaTiO₃ Integrated kV-class AlGaN/GaN Schottky Barrier Diodes with Record Average Breakdown Electric Field. , 2022, , .		0